

# 2SD1262, 2SD1262A

## Silicon NPN triple diffusion planar type darlington

For midium speed power switching

Complementary to 2SB0939, 2SB0939A

### ■ Features

- High forward current transfer ratio  $h_{FE}$
- High-speed switching
- N type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

### ■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

| Parameter                                | Symbol    | Rating                   | Unit             |   |
|--|-----------|--------------------------|------------------|---|
| Collector-base voltage<br>(Emitter open) | 2SD1262   | $V_{CBO}$                | 60               | V |
|  | 2SD1262A  |                          | 80               |   |
| Collector-emitter voltage<br>(Base open) | 2SD1262   | $V_{CEO}$                | 60               | V |
|  | 2SD1262A  |                          | 80               |   |
| Emitter-base voltage (Collector open)    | $V_{EBO}$ | 7                        | V                |   |
| Collector current                        | $I_C$     | 8                        | A                |   |
| Peak collector current                   | $I_{CP}$  | 12                       | A                |   |
| Collector power dissipation              | $P_C$     |                          | 45               | W |
|  |           | $T_a = 25^\circ\text{C}$ | 1.3              |   |
| Junction temperature                     | $T_j$     | 150                      | $^\circ\text{C}$ |   |
| Storage temperature                      | $T_{stg}$ | -55 to +150              | $^\circ\text{C}$ |   |

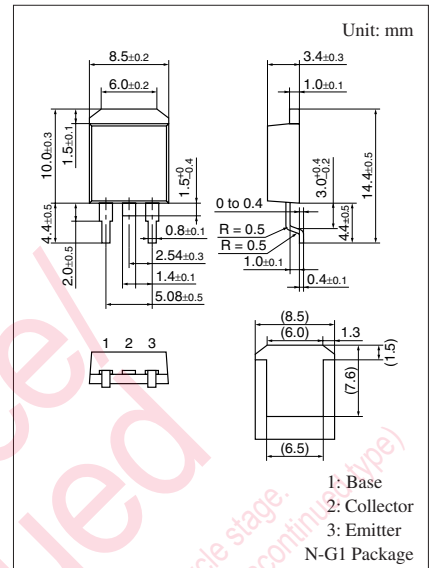
### ■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

| Parameter                                       | Symbol        | Conditions   | Min                             | Typ | Max   | Unit          |
|---|---------------|--|---------------------------------|-----|-------|---------------|
| Collector-emitter voltage<br>(Base open)        | 2SD1262       | $I_C = 30\text{ mA}, I_B = 0$                                | 60                              |     |       | V             |
|   | 2SD1262A      |  | 80                              |     |       |               |
| Collector-base cutoff<br>current (Emitter open) | 2SD1262       | $V_{CB} = 60\text{ V}, I_E = 0$                              |                                 |     | 100   | $\mu\text{A}$ |
|   | 2SD1262A      |  | $V_{CB} = 80\text{ V}, I_E = 0$ |     | 100   |               |
| Emitter-base cutoff current (Collector open)    | $I_{EBO}$     | $V_{EB} = 7\text{ V}, I_C = 0$                               |                                 |     | 2     | mA            |
| Forward current transfer ratio                  | $h_{FE1}$ *   | $V_{CE} = 3\text{ V}, I_C = 4\text{ A}$                      | 1000                            |     | 10000 | —             |
|   | $h_{FE2}$     |  | 500                             |     |       |               |
| Collector-emitter saturation voltage            | $V_{CE(sat)}$ | $I_C = 4\text{ A}, I_B = 8\text{ mA}$                        |                                 |     | 1.5   | V             |
| Base-emitter saturation voltage                 | $V_{BE(sat)}$ | $I_C = 4\text{ A}, I_B = 8\text{ mA}$                        |                                 |     | 2.0   | V             |
| Transition frequency                            | $f_T$         | $V_{CE} = 10\text{ V}, I_C = 0.5\text{ A}, f = 1\text{ MHz}$ |                                 | 20  |       | MHz           |
| Turn-on time                                    | $t_{on}$      | $I_C = 4\text{ A}$   |                                 | 0.5 |       | $\mu\text{s}$ |
| Strage time                                     | $t_{stg}$     | $I_{B1} = 8\text{ mA}, I_{B2} = -8\text{ mA}$                |                                 | 4.0 |       | $\mu\text{s}$ |
| Fall time                                       | $t_f$         |  | $V_{CC} = 50\text{ V}$          |     | 1.0   |               |

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

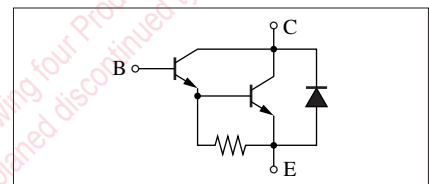
2. \*: Rank classification

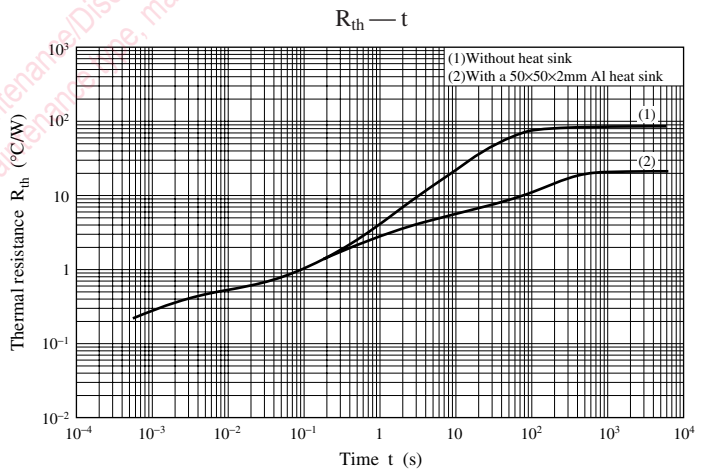
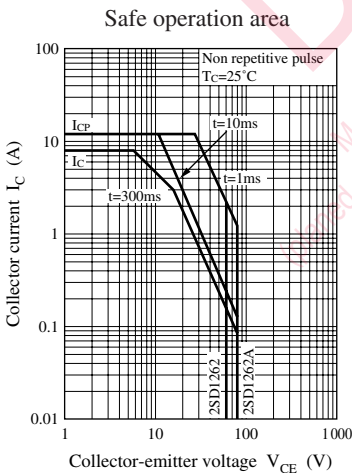
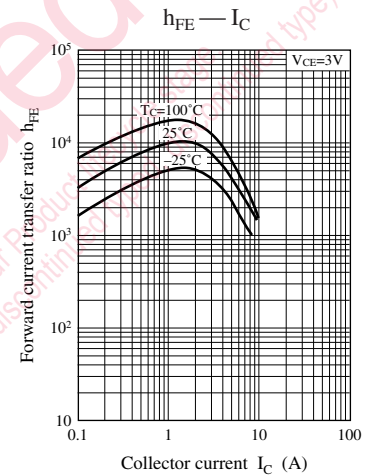
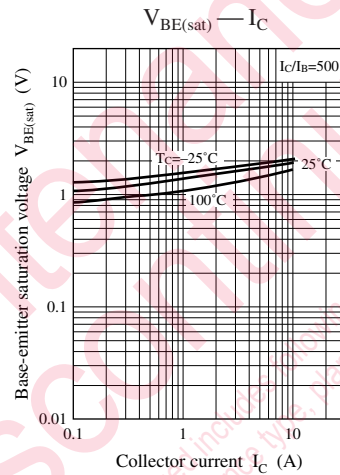
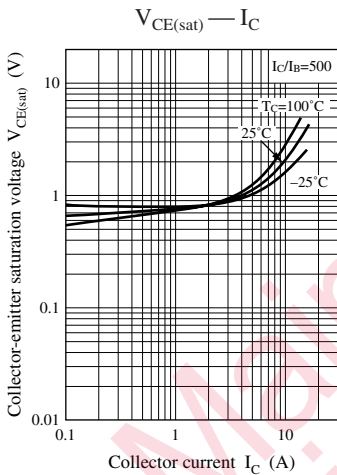
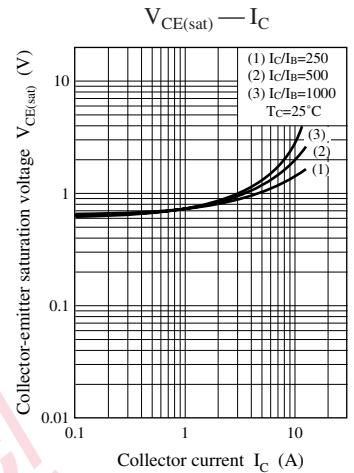
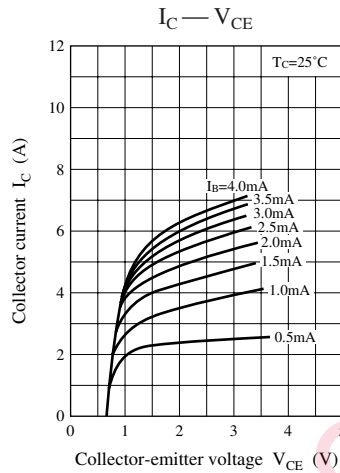
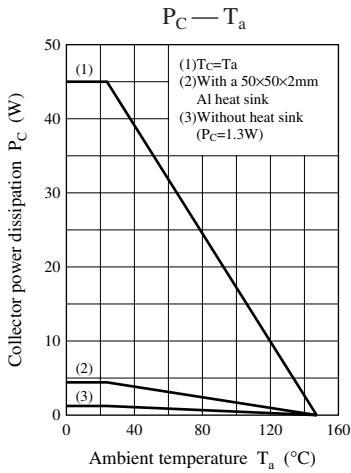
| Rank      | R            | Q            | P             |
|-----------|--------------|--------------|---------------|
| $h_{FE1}$ | 1000 to 2500 | 2000 to 5000 | 4000 to 10000 |



Note) Self-supported type package is also prepared.

### Internal Connection





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